

RESIST UNDERLAYER COATING FORMING COMPOSITION FOR FORMING PHOTO-CROSSLINKING CURED RESIST UNDERLAYER COATING

ABSTRACT

There is provided an underlayer coating that is used as an underlayer of photoresists in lithography process of the manufacture of semiconductor devices and that has a high dry etching rate in comparison to the photoresists, does not intermix with the photoresists, and is capable of flattening the surface of a semiconductor substrate having holes of a high aspect ratio; and an underlayer coating forming composition for forming the underlayer coating.

The underlayer coating forming composition for forming by light irradiation an underlayer coating used as an underlayer of a photoresist in a lithography process of the manufacture of semiconductor devices, comprises a polymerizable substance and a photopolymerization initiator.

Fig. 1